Fabrication and Crystallization Behavior of BNN Thin Films by H-MOD Process

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Ba₂NaNb₅O₁₅, hereafter called BNN, thin films are attractive candidates for nonvolatile memory and electro-optic devices. In the present work, H-MOD derived thin films in the ternary BaO-Na₂O-Nb₂O₅ phase diagram were deposited on bare silicon and Pt/Ti/SiO₂/Si substrates. XRD and SEM were used to investigate the phase evolution behavior and the microstructure of the films. It was found that the crack-free and uniform films of about 450 nm thickness were easily obtained. It was also found that Nb content strongly influenced the phase evolution of the films, in that low temperature phase was always formed if the nominal composition of stock solution was stoichiometric. However, the amount of low temperature phase decreased with the increase of excess Nb content, and the single orthorhombic tungsten bronze phase was synthesized at the temperature as low as 750°C. It is noted that the ferroelectric properties were also observed in these Nb-excess BNN thin film capacitor samples. Based on this study, the sub-solidus phase diagram below 850°C for the BaO-Na₂O-Nb₂O₅ ternary system is proposed.

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SBN 다층박막의 결정화 및 강유전 특성에 대한 산소 분압의 영향

Effect of Oxygen Pressure on the Crystallization and Ferroelectric Properties of Seeded SBN Thin Films

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 $Sr_xBa_{1-x}Nb_2O_6(0\ 25 \le x \le 0\ 75$, 이하 SBN)은 텅스텐브론즈 결정구조를 갖는 강유전체로서, 단결정의 경우 x값이 증가함에 따라 초전상수와 비선형 전광계수 값이 증가한다는 것이 알려져 있다. 최근에는 단결정에 비하여 제조가 비교적 쉬운 세라믹이나 박막을 제조하여 전자소자에 응용하기 위한 연구가 활발히 이루어지고 있다. 그러나, 박막의 경우에는 x 값이 증가함에 따라 반도체집적회로 공정에서 사용할수 있는 온도 이상으로 결정화온도가 증가하는 단점이 있다.

본 논문에서는 선행연구를 통하여 650° C 이하의 온도에서도 결정화 및 배향이 용이한 것으로 확인된 SBN30(x=0 3) 박막을 씨앗층으로 사용한 SBN60 다층박막의 결정화 거동과 강유전 특성을 보고하고자한다 박막은 이온빔 스퍼터를 이용하여 Ar/O_2 분위기에서 중착되었으며, 기판은 $Pt(100)/T_1O_2/S_1O_2/S_1$ 을 사용하였다